

2N2369A
SILICON
NPN TRANSISTOR



TO-18 CASE



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N2369A is a silicon epitaxial planar NPN transistor designed for ultra high speed saturated switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Peak Collector Current
Power Dissipation
Power Dissipation ($T_C=25^\circ\text{C}$)
Operating and Storage Junction Temperature
Thermal Resistance
Thermal Resistance

SYMBOL		UNITS
V_{CB0}	40	V
V_{CES}	40	V
V_{CEO}	15	V
V_{EBO}	4.5	V
I_C	200	mA
I_{CM}	500	mA
P_D	360	mW
P_D	1.2	W
T_J, T_{stg}	-65 to +200	$^\circ\text{C}$
θ_{JA}	486	$^\circ\text{C/W}$
θ_{JC}	146	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=20\text{V}$		400	nA
I_{CBO}	$V_{CB}=20\text{V}, T_A=150^\circ\text{C}$		30	μA
BV_{CBO}	$I_C=10\mu\text{A}$	40		V
BV_{CES}	$I_C=10\mu\text{A}$	40		V
BV_{CEO}	$I_C=10\text{mA}$	15		V
BV_{EBO}	$I_E=10\mu\text{A}$	4.5		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		200	mV
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}, T_A=125^\circ\text{C}$		300	mV
$V_{CE(SAT)}$	$I_C=30\text{mA}, I_B=3.0\text{mA}$		250	mV
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		500	mV
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	700	850	mV
$V_{BE(SAT)}$	$I_C=30\text{mA}, I_B=3.0\text{mA}$		1.15	V
$V_{BE(SAT)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		1.6	V
h_{FE}	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$	40	120	
h_{FE}	$V_{CE}=0.35\text{V}, I_C=10\text{mA}, T_A=-55^\circ\text{C}$	20		
h_{FE}	$V_{CE}=0.4\text{V}, I_C=30\text{mA}$	30		
h_{FE}	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$	20		

R1 (23-June 2014)

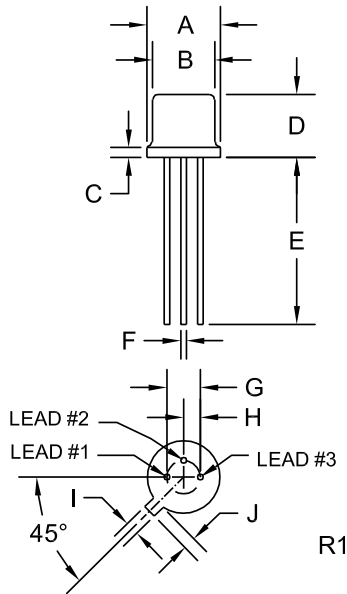
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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
f_T	$V_{CE}=10\text{V}$, $I_C=10\text{mA}$, $f=100\text{MHz}$	500		MHz
C_{ob}	$V_{CB}=5.0\text{V}$, $I_E=0$, $f=140\text{kHz}$		4.0	pF
t_{on}	$V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=3.0\text{mA}$, $I_{B2}=1.5\text{mA}$		12	ns
t_{off}	$V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=3.0\text{mA}$, $I_{B2}=1.5\text{mA}$		18	ns
t_s	$V_{CC}=10\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=10\text{mA}$		13	ns

TO-18 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.209	0.230	5.31	5.84
B (DIA)	0.178	0.195	4.52	4.95
C	-	0.030	-	0.76
D	0.170	0.210	4.32	5.33
E	0.500	-	12.70	-
F (DIA)	0.016	0.019	0.41	0.48
G (DIA)	0.100		2.54	
H	0.050		1.27	
I	0.036	0.046	0.91	1.17
J	0.028	0.048	0.71	1.22

TO-18 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING: FULL PART NUMBER

R1 (23-June 2014)